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تهران پاساژ امجد طبقه 1 واحد 16

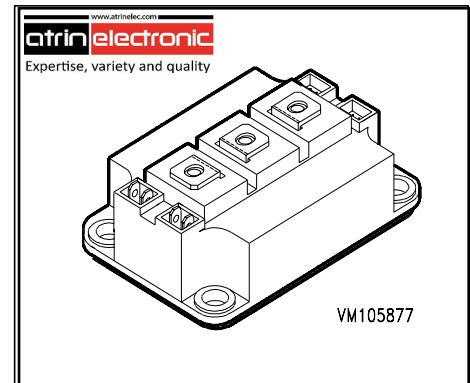


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IGBT Power Module

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate



Type	V _{CE}	I _C	Package	Ordering Code
BSM 150 GB 120 DN2	1200V	210A	HALF-BRIDGE 2	C67076-A2108-A70

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V _{CE}	1200	V
Collector-gate voltage	V _{CGR}	1200	
R _{GE} = 20 kΩ			
Gate-emitter voltage	V _{GE}	± 20	
DC collector current	I _C		A
T _C = 25 °C		210	
T _C = 80 °C		150	
Pulsed collector current, t _p = 1 ms	I _{Cpuls}		
T _C = 25 °C		420	
T _C = 80 °C		300	
Power dissipation per IGBT	P _{tot}		W
T _C = 25 °C		1250	
Chip temperature	T _j	+ 150	°C
Storage temperature	T _{stg}	-55 ... + 150	
Thermal resistance, chip case	R _{thJC}	≤ 0.1	K/W
Diode thermal resistance, chip case	R _{thJCD}	≤ 0.25	
Insulation test voltage, t = 1min.	V _{is}	2500	Vac
Creepage distance	-	20	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	-
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 6\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 150\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 150\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	- -	2.5 3.1	3 3.7	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	- -	2 8	2.8 -	mA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	320	nA

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 150\text{ A}$	g_{fs}	62	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	11	-	nF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	1.6	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	0.6	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 150\text{ A}$ $R_{Gon} = 5.6\ \Omega$	$t_{d(on)}$	-	200	400	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 150\text{ A}$ $R_{Gon} = 5.6\ \Omega$	t_r	-	100	200	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 150\text{ A}$ $R_{Goff} = 5.6\ \Omega$	$t_{d(off)}$	-	600	800	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 150\text{ A}$ $R_{Goff} = 5.6\ \Omega$	t_f	-	70	100	

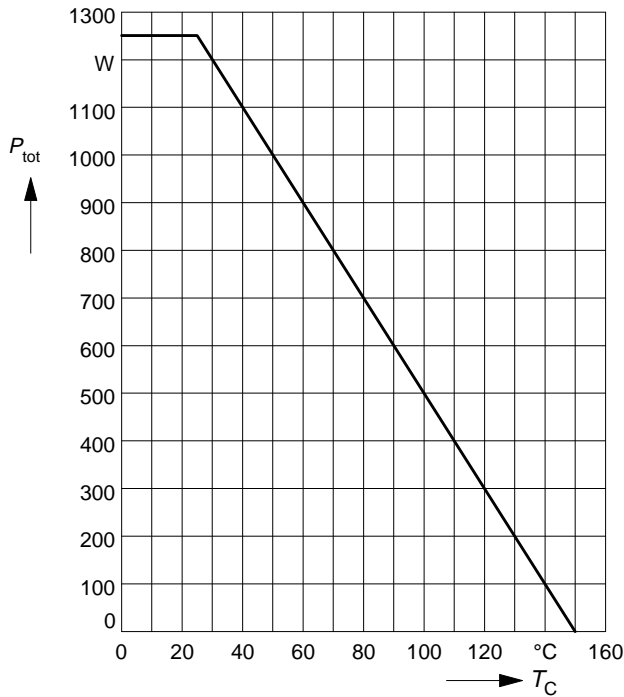
Free-Wheel Diode

Diode forward voltage $I_F = 150\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 150\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	2.3	2.8	V
Reverse recovery time $I_F = 150\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -1500\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	0.4	-	
Reverse recovery charge $I_F = 150\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -1500\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rr}	-	5	-	μC
		-	18	-	

Power dissipation

$$P_{\text{tot}} = f(T_C)$$

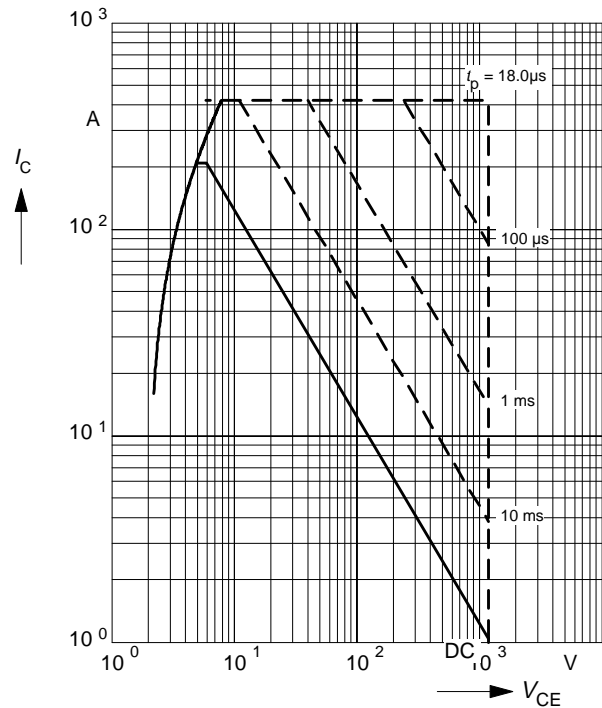
parameter: $T_j \leq 150^\circ\text{C}$



Safe operating area

$$I_C = f(V_{\text{CE}})$$

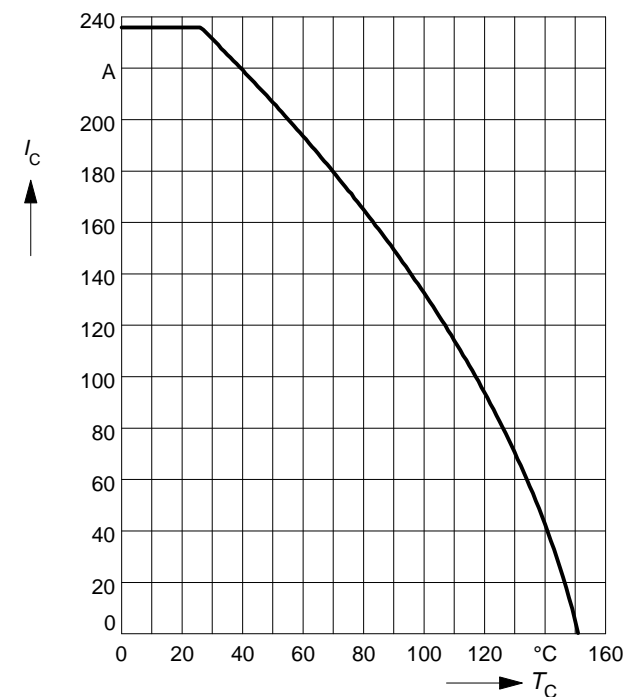
parameter: $D = 0, T_C = 25^\circ\text{C}, T_j \leq 150^\circ\text{C}$



Collector current

$$I_C = f(T_C)$$

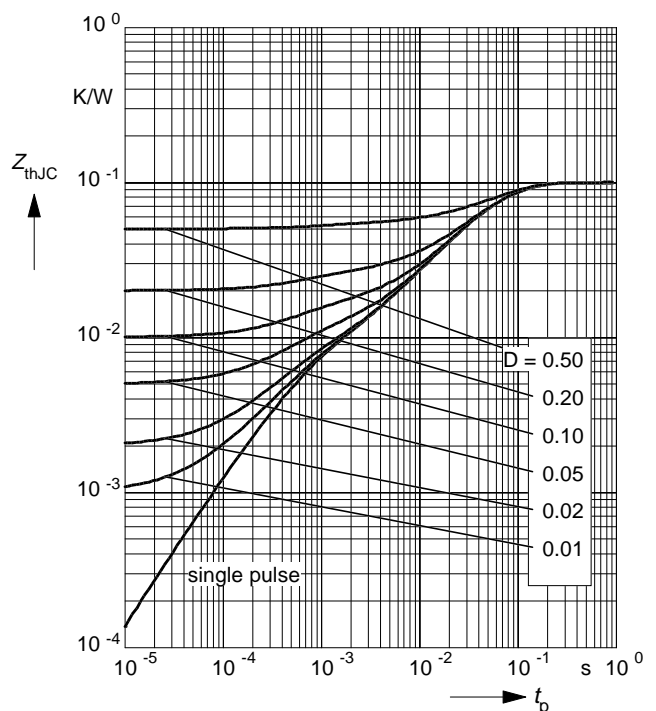
parameter: $V_{\text{GE}} \geq 15\text{ V}, T_j \leq 150^\circ\text{C}$



Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

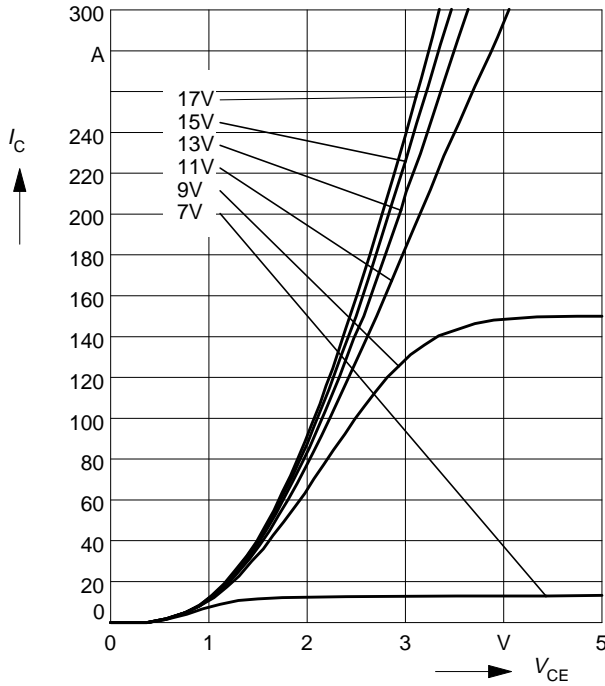
parameter: $D = t_p / T$



Typ. output characteristics

$$I_C = f(V_{CE})$$

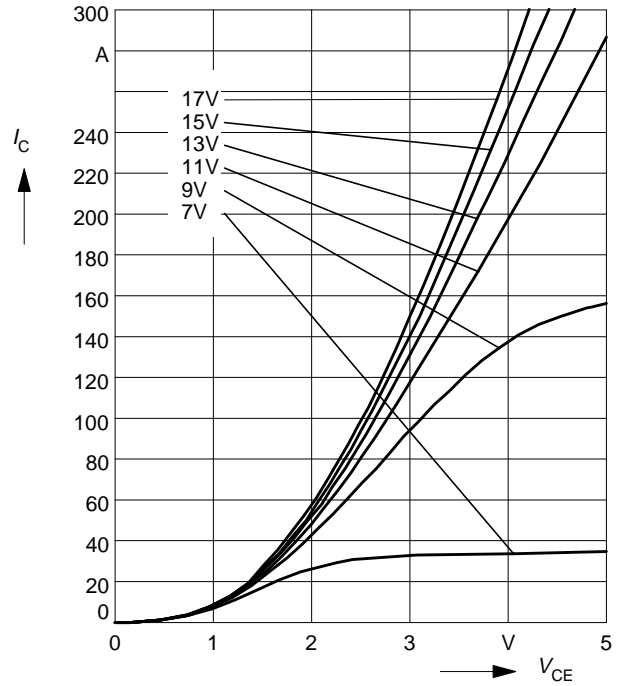
parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



Typ. output characteristics

$$I_C = f(V_{CE})$$

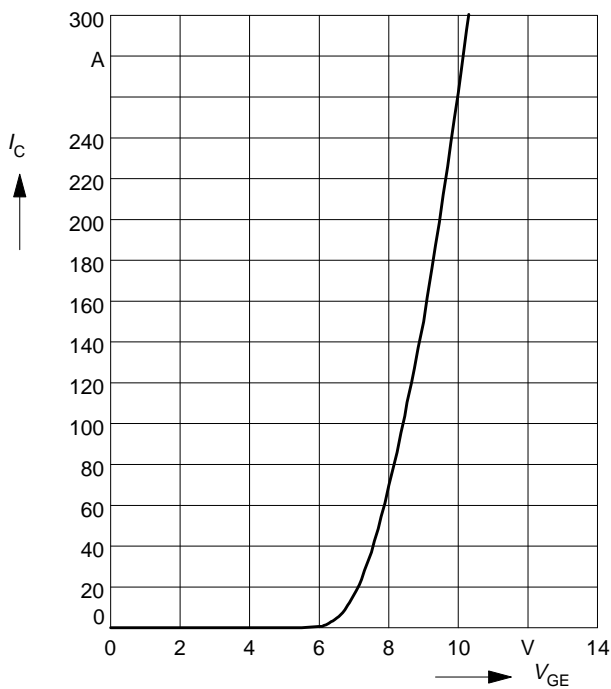
parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$



Typ. transfer characteristics

$$I_C = f(V_{GE})$$

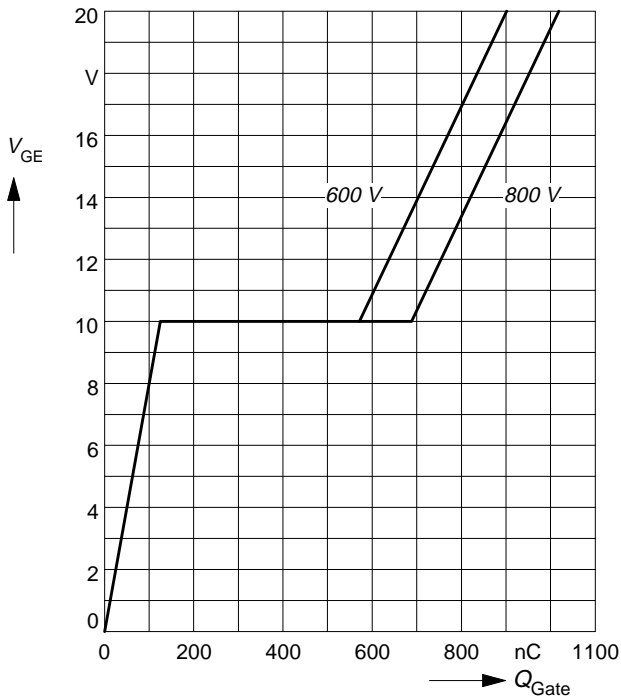
parameter: $t_p = 80 \mu s$, $V_{CE} = 20 V$



Typ. gate charge

$$V_{GE} = f(Q_{Gate})$$

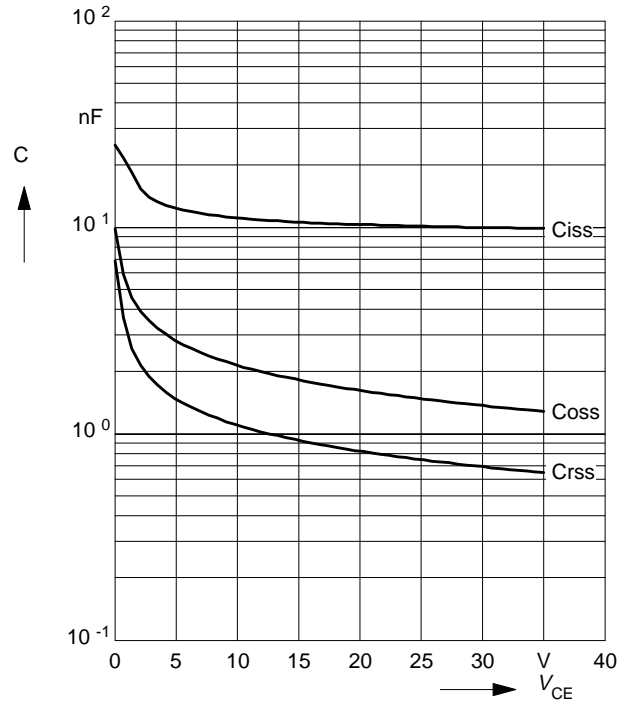
parameter: $I_{C\ puls} = 150\ A$



Typ. capacitances

$$C = f(V_{CE})$$

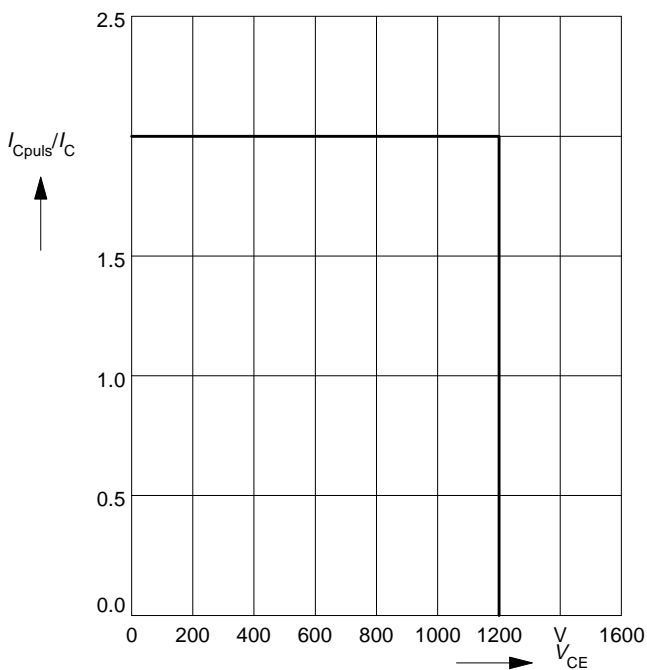
parameter: $V_{GE} = 0\ V, f = 1\ MHz$



Reverse biased safe operating area

$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

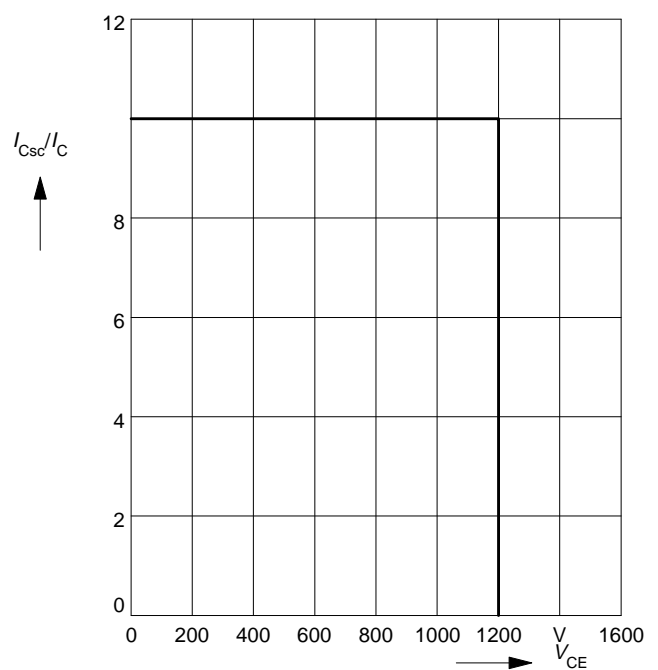
parameter: $V_{GE} = 15\ V$



Short circuit safe operating area

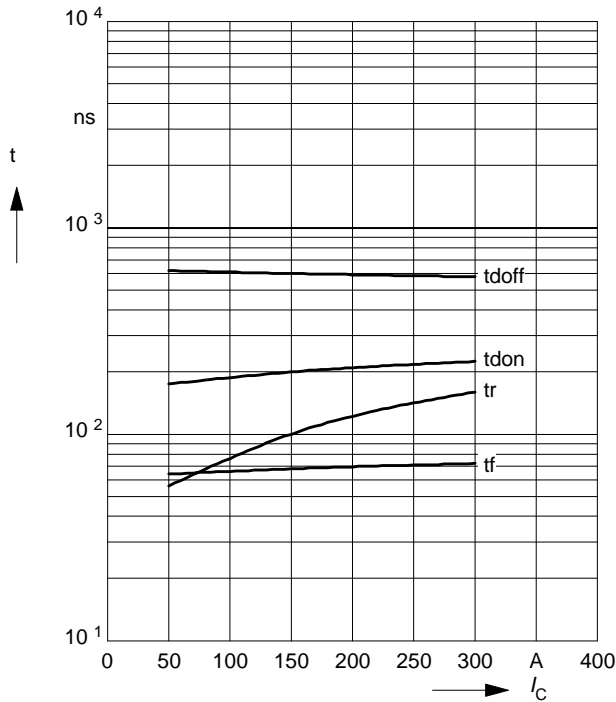
$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

parameter: $V_{GE} = \pm 15\ V, t_{SC} \le 10\ \mu s, L < 25\ nH$



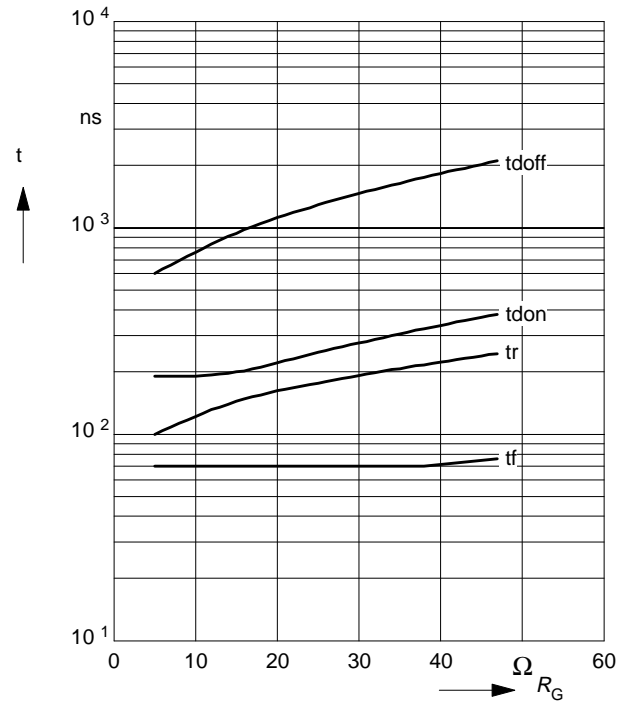
Typ. switching time

$t = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 5.6\ \Omega$



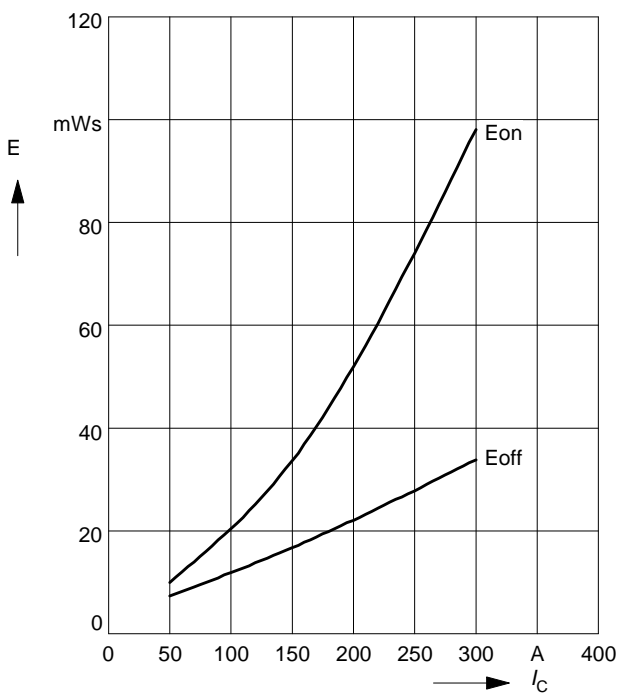
Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$



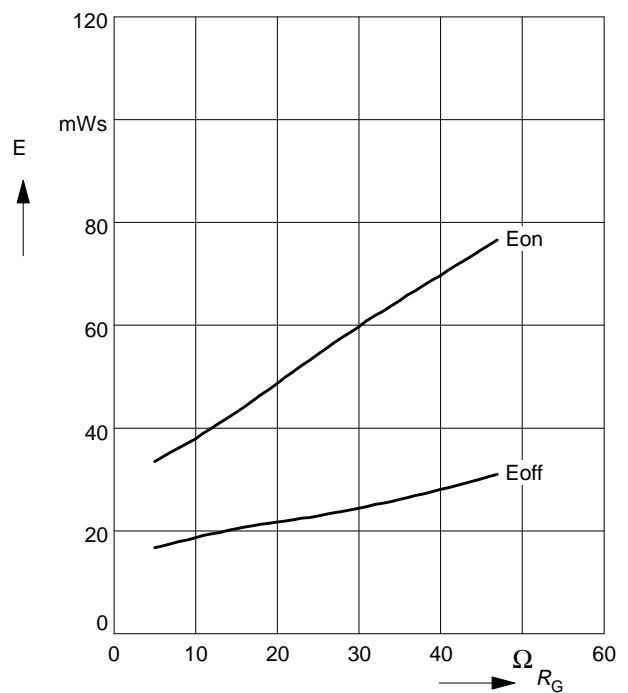
Typ. switching losses

$E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 5.6\ \Omega$



Typ. switching losses

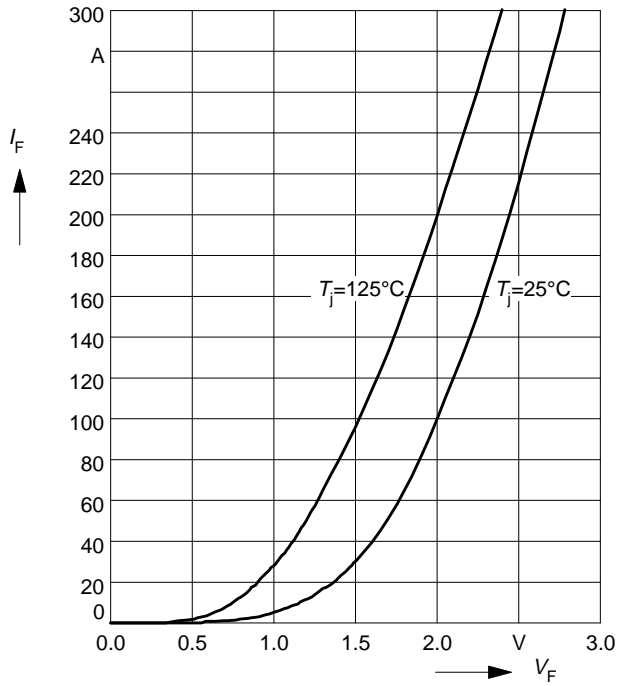
$E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$



Forward characteristics of fast recovery reverse diode

$I_F = f(V_F)$

parameter: T_j



Transient thermal impedance Diode

$Z_{thJC} = f(t_p)$

parameter: $D = t_p / T$

